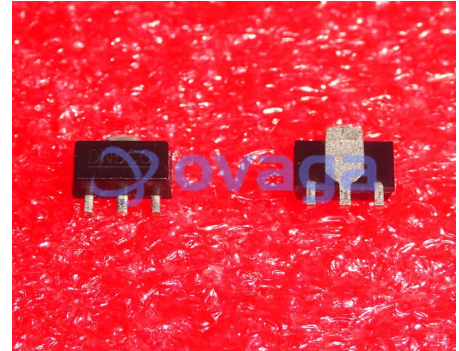


N-Channel Depletion-Mode Vertical DMOS FETs, MOSFET 250V 60hm

Manufacturers	Microchip Technology, Inc
Package/Case	SOT-89-3
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for DN3525N8-G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

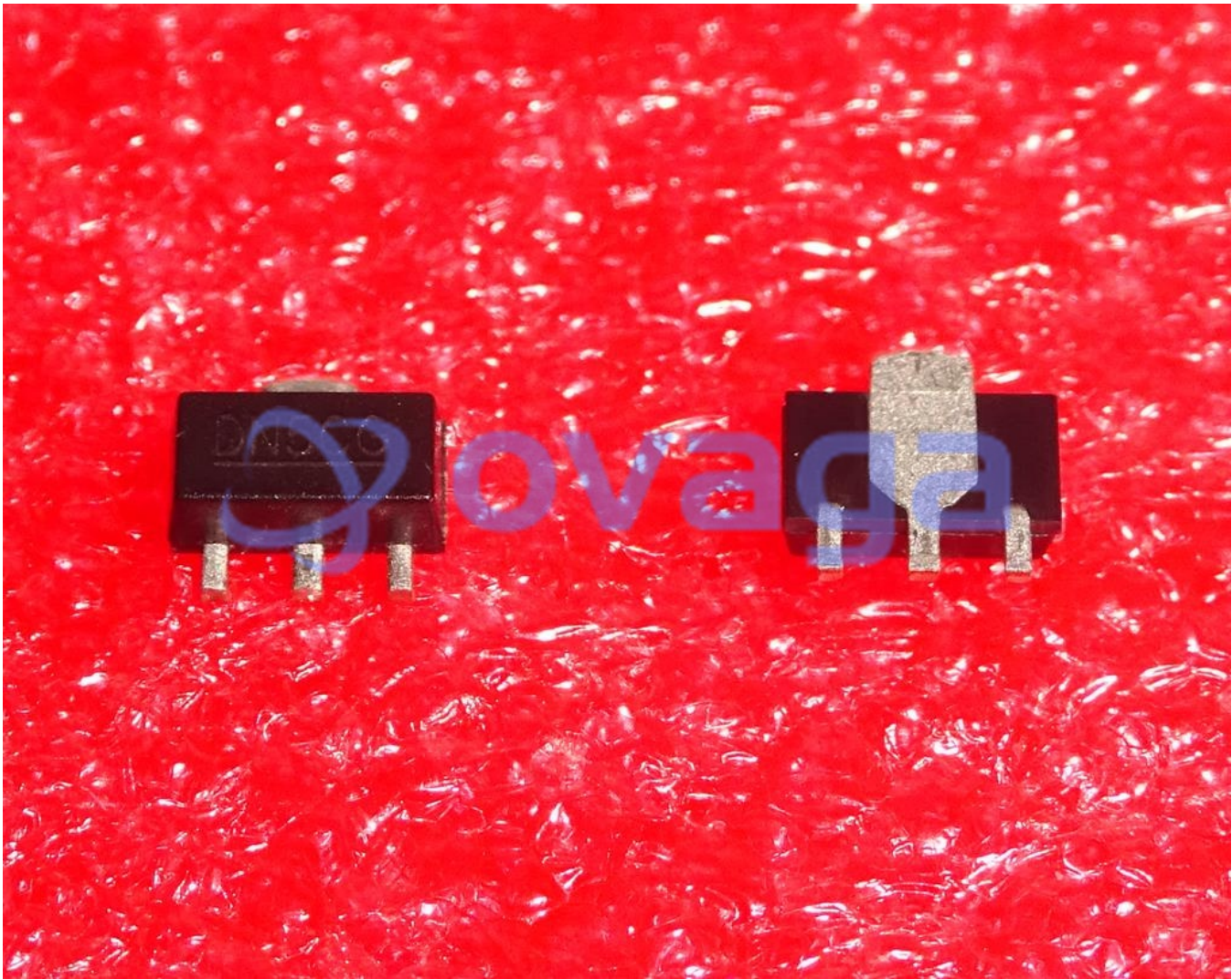
[RFQ](#)

General Description

DN3525 is a low threshold depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown. Vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Features

- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage



Related Products



[DN3135K1-G](#)

Microchip Technology, Inc
SOT-23 (TO-236AB)



[TN2524N8-G](#)

Microchip Technology, Inc
SOT-89



[APT5010JFLL](#)

Microchip Technology, Inc
SOT227



[DN2625DK6-G](#)

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97A/200V/MOS/1U



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